

ABSTRACT

This invention provides a method for forming a semiconductor device, capable of preventing as many impurities as possible, which cause deterioration in film quality, from existing in an gate insulating film.

In this invention, a step of forming an insulating film so as to have a thickness in the range of 0.3 to 2 nm and a step of removing impurities from the insulating film are repeated a plurality of times, to form an insulating film having a prescribed thickness.